/ Descriptions

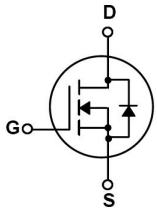
TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

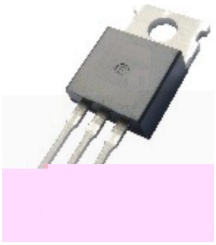
/ Features

Low gate charge, low crss, fast switching.

/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.





PIN1 G PIN 2 D PIN 3 S

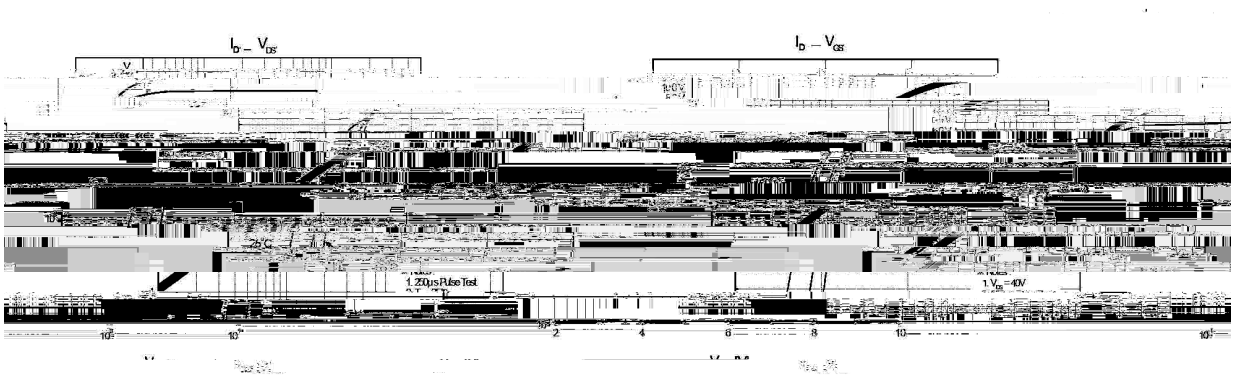
/ h_{FE} Classifications & Marking

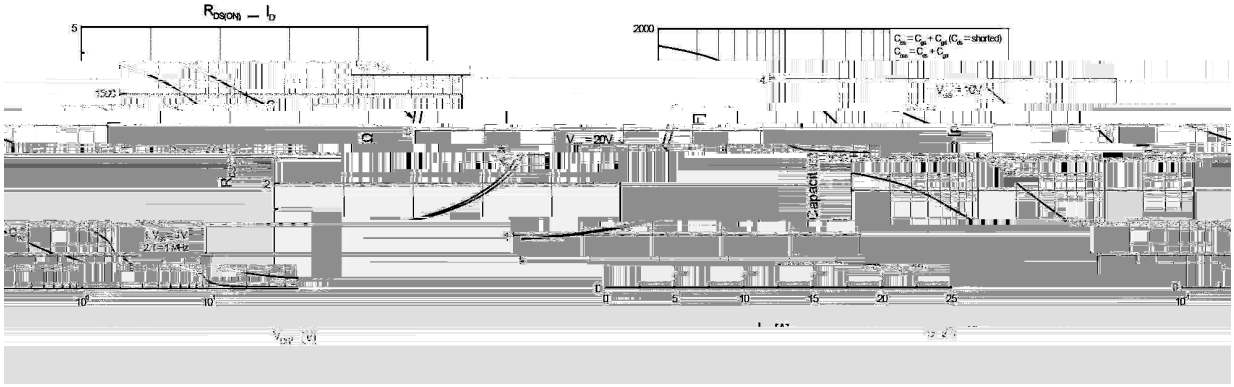
See Marking Instructions.

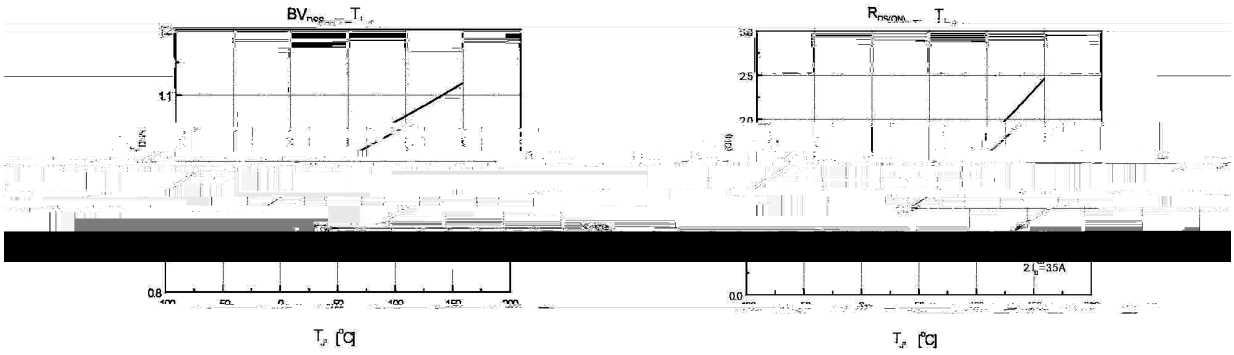
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	7.0	A
Drain Current	I_D(Tc=100)	4.4	A
Drain Current - Pulsed	I_{DM}	28	A
Gate-Source Voltage	V_{GS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	420	mJ
Repetitive Avalanche Energy	E_{AR}	14.7	mJ
Avalanche Current	I_{AR}	7.0	A
Power Dissipation	P_D(Tc=25)	147	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

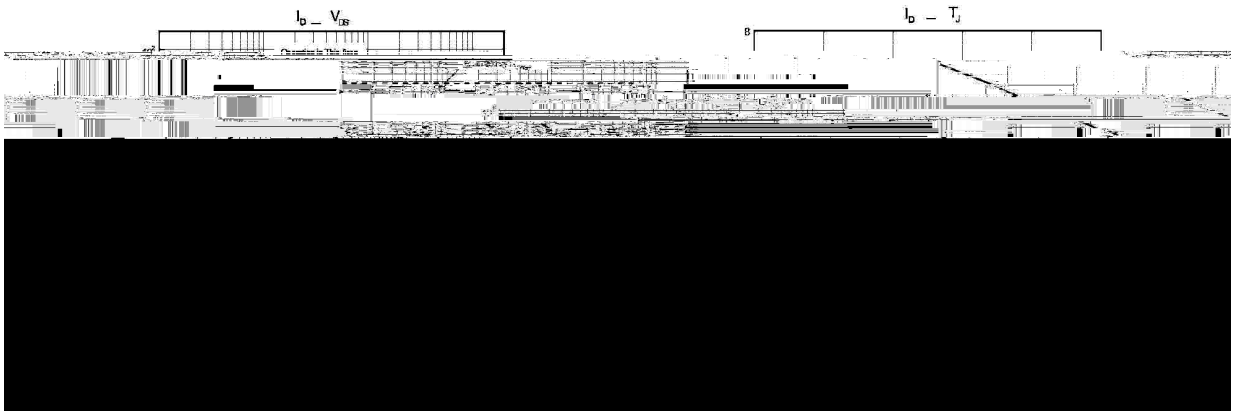
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V	I_D=250μA	650			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=650V	V_{GS}=0V			1.0	μA
		V_{DS}=520V	T_C=125			100	μA
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±30V	V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V	I_D=3.5A			1.3	Ω
Forward Transconductance	g_{FS}	V_{DS}=40V	I_D=3.5A		8.2		S
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_S=7.0A			1.4	V
Input Capacitance	C_{iss}	V_{DS}=25V f=1.0MHz	V_{GS}=0V		1100	1500	pF
Output Capacitance	C_{oss}				110	150	pF

/ Electrical Characteristic Curve

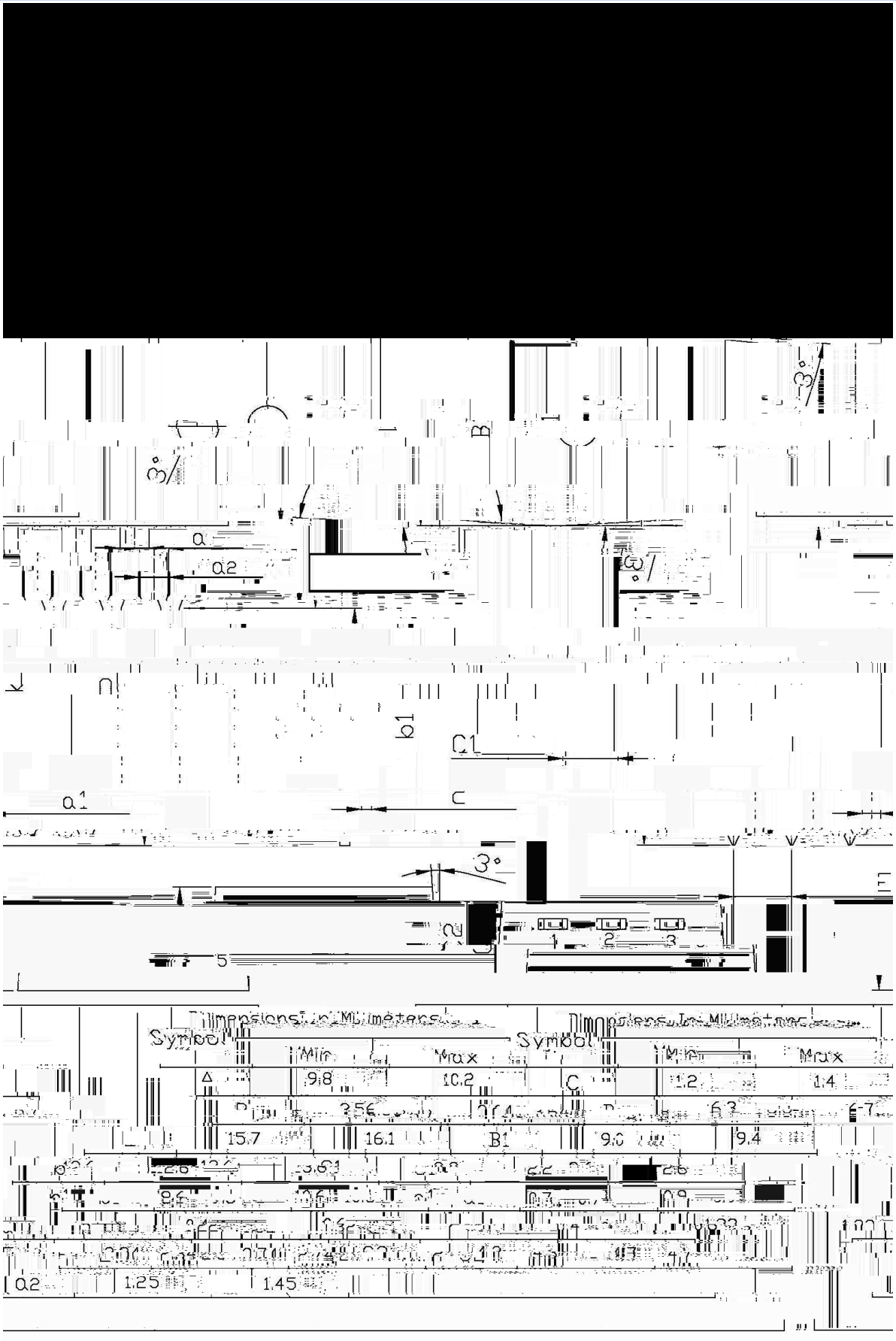




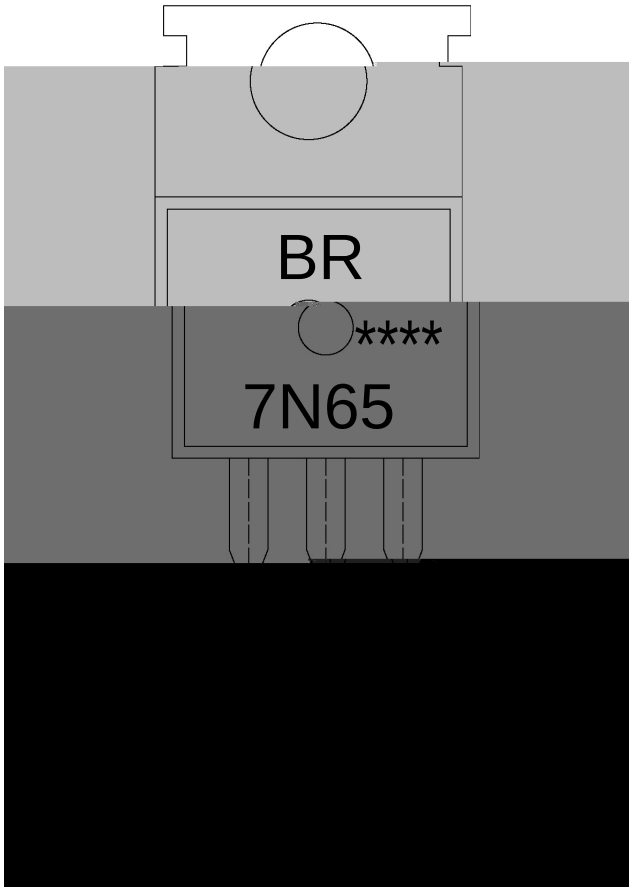




/ Package Dimensions



/ Marking Instructions

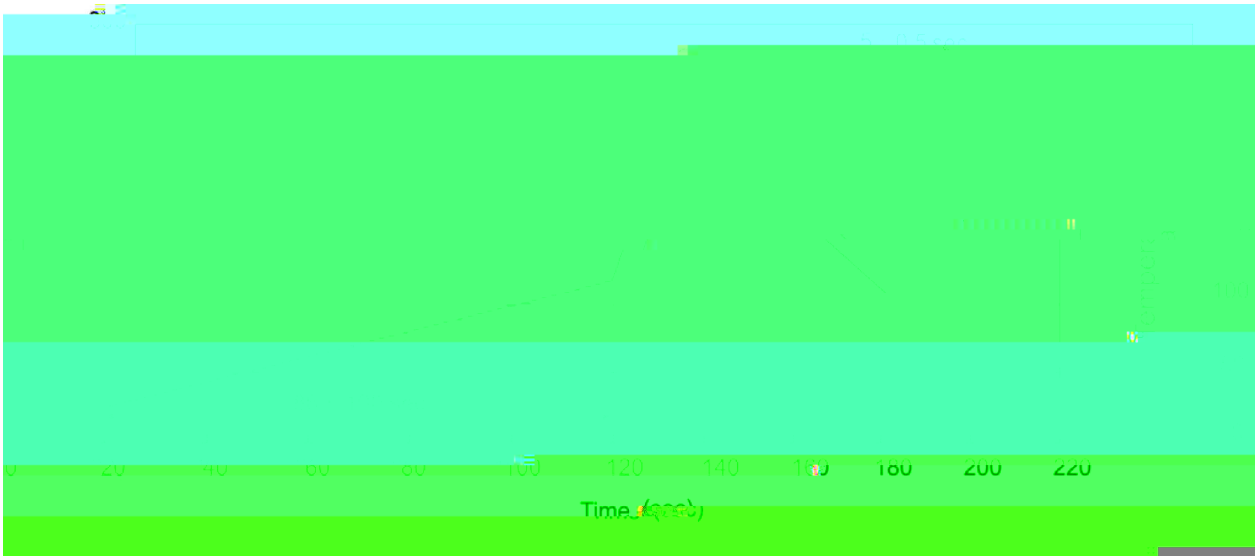


BR

Note:

BR:	Company Code
7N65:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150